RENESAS

DATASHEET

HIP4080A

80V/2.5A Peak, High Frequency Full Bridge FET Driver

The HIP4080A is a high frequency, medium voltage Full Bridge N-Channel FET driver IC, available in 20 lead plastic SOIC and DIP packages. The HIP4080A includes an input comparator, used to facilitate the "hysteresis" and PWM modes of operation. Its HEN (high enable) lead can force current to freewheel in the bottom two external power MOSFETs, maintaining the upper power MOSFETs off. Since it can switch at frequencies up to 1MHz, the HIP4080A is well suited for driving Voice Coil Motors, switching power amplifiers and power supplies.

HIP4080A can also drive medium voltage brush motors, and two HIP4080As can be used to drive high performance stepper motors, since the short minimum "on-time" can provide fine micro-stepping capability.

Short propagation delays of approximately 55ns maximize control loop crossover frequencies and dead-times which can be adjusted to near zero to minimize distortion, resulting in precise control of the driven load.

The similar HIP4081A IC allows independent control of all 4 FETs in a Full Bridge configuration.

The Application Note for the HIP4080A is AN9404.

Ordering Information

PART NUMBER	TEMPERATURE RANGE (°C)	PACKAGE (RoHS Compliant)	PKG. DWG. #
HIP4080AIPZ (Note 1)	-40 to +85	20 Ld PDIP	E20.3
HIP4080AIBZ (Note 1)	-40 to +85	20 Ld SOIC	M20.3

NOTES:

- Intersil Pb-Free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which is compatible with both SnPb and Pb-free soldering operations. Intersil Pb-Free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pbfree requirements of IPC/JEDEC J Std-020B.
- 2. Add "T" suffix for Tape and Reel packing option. HIP4080AIP not available in Tape and Reel.

Features

- Drives N-Channel FET Full Bridge Including High Side Chop Capability
- Bootstrap Supply Max Voltage to 95VDC
- Drives 1000pF Load at 1MHz in Free Air at +50°C with Rise and Fall Times of Typically 10ns
- User-Programmable Dead Time
- Charge-Pump and Bootstrap Maintain Upper Bias Supplies
- DIS (Disable) Pin Pulls Gates Low
- Input Logic Thresholds Compatible with 5V to 15V Logic Levels
- Very Low Power Consumption
- Undervoltage Protection
- Pb-Free (RoHS Compliant)

Applications

- Medium/Large Voice Coil Motors
- Full Bridge Power Supplies
- Switching Power Amplifiers
- High Performance Motor Controls
- Noise Cancellation Systems
- Battery Powered Vehicles
- Peripherals
- U.P.S.

Pinout



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Application Block Diagram



Functional Block Diagram (1/2 HIP4080A)



Typical Application (Hysteresis Mode Switching)





Absolute Maximum Ratings

Logic I/O Voltages
Voltage on AHS, BHS6.0V (Transient) to 70V (-55°C to 125°C)
Voltage on ALS, BLS2.0V (Transient) to +2.0V (Transient)
$\label{eq:Voltage on AHB, BHB V_{AHS, BHS} -0.3V to V_{AHS, BHS} +V_{DD} \\ Voltage on ALO, BLO V_{ALS, BLS} -0.3V to V_{CC} +0.3V \\ Voltage on AHO, BHO V_{AHS, BHS} -0.3V to V_{AHB, BHB} +0.3V \\ Input Current, HDEL and LDEL5mA to 0mA \\ Phase Slew Rate 20V/ns \\ All Voltages relative to V_{SS}, unless otherwise specified. \\ \end{tabular}$

Operating Conditions

Supply Voltage, V _{DD} and V _{CC} +9.5V to +15V
Voltage on ALS, BLS
Voltage on AHB, BHB V _{AHS, BHS} +5V to V _{AHS, BHS} +15V
Input Current, HDEL and LDEL
Operating Ambient Temperature Range40°C to +85°C

Thermal Information

Thermal Resistance (Typical, Note 3)	θ _{JA} (°C/W)
SOIC Package	85
PDIP Package	
Maximum Power Dissipation at +85°C	
SOIC Package	470mW
PDIP Package	530mW
Storage Temperature Range65°	C to +150°C
Operating Max. Junction Temperature	+125°C
Lead Temperature (Soldering 10s)	+300°C
(For SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Electrical Specifications	$V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V$, $R_{HDEL} = R_{LDEL} = 100K$, and
	T _A = +25°C, Unless Otherwise Specified

		_		T _J = +25°C			T _J = - 40°C TO +125°C			
PARAMETERS	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	MAX	UNITS		
SUPPLY CURRENTS AND CHARGE PUMPS										
V _{DD} Quiescent Current	I _{DD}	IN- = 2.5V, Other Inputs = 0V	8	11	14	7	14	mA		
V _{DD} Operating Current	I _{DDO}	Outputs switching f = 500kHz, No Load		12	15	8	15	mA		
V _{CC} Quiescent Current	Icc	N- = 2.5V, Other Inputs = 0V, $ALO = I_{BLO} = 0$		25	80	-	100	μA		
V _{CC} Operating Current	Icco	f = 500kHz, No Load	1	1.25	2.0	0.8	3	mA		
AHB, BHB Quiescent Current - Qpump Output Current	I _{AHB} , I _{BHB}	IN- = 2.5V, Other Inputs = 0V, I _{AHO} = I _{BHO} = 0, V _{DD} = V _{CC} =V _{AHB} = V _{BHB} = 10V	-50	-25	-11	-60	-10	μA		
AHB, BHB Operating Current	I _{AHBO} , I _{BHBO}	f = 500kHz, No Load	0.62	1.2	1.5	0.5	1.9	mA		
AHS, BHS, AHB, BHB Leakage Current	IHLK	V _{BHS} = V _{AHS} = 80V, V _{AHB} = V _{BHB} = 93V	-	0.02	1.0	-	10	μA		
AHB-AHS, BHB-BHS Qpump Output Voltage	V _{AHB} - V _{AHS} V _{BHB} - V _{BHS}	I _{AHB} = I _{AHB} = 0, No Load	11.5	12.6	14.0	10.5	14.5	V		
INPUT COMPARATOR PINS: IN+, IN-,	OUT									
Offset Voltage	V _{OS}	Over Common Mode Voltage Range	-10	0	+10	-15	+15	mV		
Input Bias Current	I _{IB}		0	0.5	2	0	4	μA		
Input Offset Current	I _{OS}		-1	0	+1	-2	+2	μA		
Input Common Mode Voltage Range	CMVR		1	-	V _{DD} -1.5	1	V _{DD} -1.5	V		



Electrical Specifications

 $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V, V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V, R_{HDEL} = R_{LDEL} = 100K, and T_A = +25^{\circ}C$, Unless Otherwise Specified (Continued)

			т	T _J = +25°C			T _J = - 40°C TO +125°C		
PARAMETERS	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN MAX			
Voltage Gain	AVOL		10	25	-	10	-	V/mV	
OUT High Level Output Voltage	V _{OH}	IN+ > IN-, I _{OH} = -250µA	V _{DD} -0.4	-	-	V _{DD} - 0.5	-	V	
OUT Low Level Output Voltage	V _{OL}	IN+ < IN-, I _{OL} = +250μA	-	-	0.4	-	0.5	V	
Low Level Output Current	I _{OL}	V _{OUT} = 6V 6.5 14 19		19	6	20	mA		
High Level Output Current	I _{OH}	0H V _{OUT} = 6V -17 -10 -3		-20	-2.5	mA			
INPUT PINS: DIS						1			
Low Level Input Voltage	VIL	Full Operating Conditions	-	-	1.0	-	0.8	V	
High Level Input Voltage	VIH	Full Operating Conditions	2.5	-	-	2.7	-	V	
Input Voltage Hysteresis	Itage Hysteresis - 35 -		-	-	-	mV			
Low Level Input Current	IIL	V _{IN} = 0V, Full Operating Conditions	-130	-100	-75	-135	-65	μA	
High Level Input Current	IIH	V _{IN} = 5V, Full Operating Conditions	-1	-	+1	-10	+10	μA	
INPUT PINS: HEN									
Low Level Input Voltage	VIL	Full Operating Conditions	-	-	1.0	-	0.8	V	
High Level Input Voltage	VIH	Full Operating Conditions	2.5	-	-	2.7	-	V	
Input Voltage Hysteresis			-	35	-	-	-	mV	
Low Level Input Current	IIL	V _{IN} = 0V, Full Operating Conditions	-260	-200	-150	-270	-130	μA	
High Level Input Current	IIH	V _{IN} = 5V, Full Operating Conditions	-1	-	+1	-10	+10	μA	
TURN-ON DELAY PINS: LDEL AND	HDEL			1		1	1		
LDEL, HDEL Voltage	V _{HDEL,} V	$I_{HDEL} = I_{LDEL} = -100 \mu A$	4.9	5.1	5.3	4.8	5.4	V	
GATE DRIVER OUTPUT PINS: ALO,	BLO, AHO, AN	D BHO		r			r		
Low Level Output Voltage	V _{OL}	I _{OUT} = 100mA	0.7	0.85	1.0	0.5	1.1	V	
High Level Output Voltage	V _{CC} - V _{OH}	I _{OUT} = -100mA	0.8	0.95	1.1	0.5	1.2	V	
Peak Pullup Current	I _O +	V _{OUT} = 0V	1.7	2.6	3.8	1.4	4.1	А	
Peak Pulldown Current	I _O -	V _{OUT} = 12V	1.7	2.4	3.3	1.3	3.6	А	
Under Voltage, Rising Threshold	UV+		8.1	8.8	9.4	8.0	9.5	V	
Under Voltage, Falling Threshold	UV-		7.6	8.3	8.9	7.5	9.0	V	
Under Voltage, Hysteresis	HYS		0.25	0.4	0.65	0.2	0.7	V	

Switching Specifications $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = 0V$, $R_{HDEL} = R_{LDEL} = 10K$, $C_L = 1000pF$, and $T_A = +25^{\circ}C$, Unless Otherwise Specified

			T _J = +25°C			T _J = - 40°C TO +125°C		
PARAMETERS	SYMBOL	TEST CONDITIONS	MIN	ТҮР	МАХ	MIN	MAX	UNITS
Lower Turn-off Propagation Delay (IN+/IN- to ALO/BLO)	T _{LPHL}		-	40	70	-	90	ns
Upper Turn-off Propagation Delay (IN+/IN- to AHO/BHO)	T _{HPHL}		-	50	80	-	110	ns
Lower Turn-on Propagation Delay (IN+/IN- to ALO/BLO)	T _{LPLH}		-	40	70	-	90	ns
Upper Turn-on Propagation Delay (IN+/IN- to AHO/BHO)	T _{HPLH}		-	70	110	-	140	ns
Rise Time	Τ _R		-	10	25	-	35	ns
Fall Time	Τ _F		-	10	25	-	35	ns
Turn-on Input Pulse Width	T _{PWIN-ON}		50	-	-	50	-	ns
Turn-off Input Pulse Width	T _{PWIN-OFF}		40	-	-	40	-	ns
Disable Turn-off Propagation Delay (DIS - Lower Outputs)	T _{DISLOW}		-	45	75	-	95	ns
Disable Turn-off Propagation Delay (DIS - Upper Outputs)	T _{DISHIGH}		-	55	85	-	105	ns
Disable to Lower Turn-on Propagation Delay (DIS - ALO and BLO)	T _{DLPLH}		-	45	70	-	90	ns
Refresh Pulse Width (ALO and BLO)	T _{REF-PW}		240	380	500	200	600	ns
Disable to Upper Enable (DIS - AHO and BHO)	T _{UEN}		-	480	630	-	750	ns
HEN-AHO, BHO Turn-off, Propagation Delay	T _{HEN-PHL}	R _{HDEL} = R _{LDEL} = 10K	-	40	70	-	90	ns
HEN-AHO, BHO Turn-on, Propagation Delay	T _{HEN-PLH}	R _{HDEL} = R _{LDEL} = 10K	-	60	90	-	110	ns

TRUTH TABLE

	INPU	JT			OUT	PUT	
IN+ > IN-	HEN	U/V	DIS	ALO	AHO	BLO	вно
Х	Х	Х	1	0	0	0	0
0	0	0	0	1	0	0	0
1	1	0	0	0	1	1	0
0	1	0	0	1	0	0	1
1	0	0	0	0	0	1	0
Х	Х	1	Х	0	0	0	0

Pin Descriptions

PIN NUMBER	SYMBOL	DESCRIPTION
1	BHB	B High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30µA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
2	HEN	High-side Enable input. Logic level input that when low overrides IN+/IN- (Pins 6 and 7) to put AHO and BHO drivers (Pins 11 and 20) in low output state. When HEN is high AHO and BHO are controlled by IN+/IN- inputs. The pin can be driven by signal levels of 0V to 15V (no greater than V _{DD}).
3	DIS	DISable input. Logic level input that when taken high sets all four outputs low. DIS high overrides all other inputs. When DIS is taken low the outputs are controlled by the other inputs. The pin can be driven by signal levels of 0V to $15V$ (no greater than V _{DD}).
4	V _{SS}	Chip negative supply, generally will be ground.
5	OUT	OUTput of the input control comparator. This output can be used for feedback and hysteresis.
6	IN+	Noninverting input of control comparator. If IN+ is greater than IN- (Pin 7) then ALO and BHO are low level outputs and BLO and AHO are high level outputs. If IN+ is less than IN- then ALO and BHO are high level outputs and BLO and AHO are low level outputs. DIS (Pin 3) high level will override IN+/IN- control for all outputs. HEN (Pin 2) low level will override IN+/IN- control of AHO and BHO. When switching in four quadrant mode, dead time in a half bridge leg is controlled by HDEL and LDEL (Pins 8 and 9).
7	IN-	Inverting input of control comparator. See IN+ (Pin 6) description.
8	HDEL	High-side turn-on DELay. Connect resistor from this pin to V _{SS} to set timing current that defines the turn-on delay of both high-side drivers. The low-side drivers turn-off with no adjustable delay, so the HDEL resistor guarantees no shoot-through by delaying the turn-on of the high-side drivers. HDEL reference voltage is approximately 5.1V.
9	LDEL	Low-side turn-on DELay. Connect resistor from this pin to V _{SS} to set timing current that defines the turn-on delay of both low-side drivers. The high-side drivers turn-off with no adjustable delay, so the LDEL resistor guarantees no shoot-through by delaying the turn-on of the low-side drivers. LDEL reference voltage is approximately 5.1V.
10	AHB	A High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30µA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
11	AHO	A High-side Output. Connect to gate of A High-side power MOSFET.
12	AHS	A High-side Source connection. Connect to source of A High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
13	ALO	A Low-side Output. Connect to gate of A Low-side power MOSFET.
14	ALS	A Low-side Source connection. Connect to source of A Low-side power MOSFET.
15	V _{CC}	Positive supply to gate drivers. Must be same potential as V _{DD} (Pin 16). Connect to anodes of two bootstrap diodes
16	V _{DD}	Positive supply to lower gate drivers. Must be same potential as V _{CC} (Pin 15). De-couple this pin to V _{SS} (Pin 4).
17	BLS	B Low-side Source connection. Connect to source of B Low-side power MOSFET.
18	BLO	B Low-side Output. Connect to gate of B Low-side power MOSFET.
19	BHS	B High-side Source connection. Connect to source of B High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
20	BHO	B High-side Output. Connect to gate of B High-side power MOSFET.

Timing Diagrams



FIGURE 1. BISTATE MODE



FIGURE 2. HIGH SIDE CHOP MODE



FIGURE 3. DISABLE FUNCTION

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V$, $R_{HDEL} = R_{LDEL} = 100K$, and $T_A = +25^{\circ}C$, Unless Otherwise Specified







FIGURE 6. SIDE A, B FLOATING SUPPLY BIAS CURRENT vs FREQUENCY (LOAD = 1000pF)





FIGURE 5. I_{DDO} NO-LOAD I_{DD} SUPPLY CURRENT vs FREQUENCY (kHz)



FIGURE 7. I_{CCO}, NO-LOAD I_{CC} SUPPLY CURRENT vs FREQUENCY (kHz) TEMPERATURE





Typical Performance Curves $v_{DD} = v_{CC} = v_{AHB} = v_{BHB} = 12V$, $v_{SS} = v_{ALS} = v_{BLS} = v_{AHS} = v_{BHS} = 0V$, $R_{HDEL} = R_{LDEL} = 100K$, and $T_A = +25^{\circ}C$, Unless Otherwise Specified (Continued)







FIGURE 12. AHB - AHS, BHB - BHS NO-LOAD CHARGE PUMP VOLTAGE vs TEMPERATURE





FIGURE 11. HEN LOW LEVEL INPUT CURRENT I_{IL} vs TEMPERATURE



FIGURE 13. UPPER DISABLE TURN-OFF PROPAGATION DELAY T_{DISHIGH} vs TEMPERATURE



FIGURE 15. LOWER DISABLE TURN-OFF PROPAGATION DELAY T_{DISLOW} vs TEMPERATURE











FIGURE 18. UPPER TURN-OFF PROPAGATION DELAY THPHL vs TEMPERATURE





FIGURE 17. DISABLE TO LOWER ENABLE TDLPLH **PROPAGATION DELAY vs TEMPERATURE**



FIGURE 19. UPPER TURN-ON PROPAGATION DELAY THPLH vs TEMPERATURE



vs TEMPERATURE

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Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V$, $R_{HDEL} = R_{LDEL} = 100K$, and $T_A = +25^{\circ}C$, Unless Otherwise Specified



FIGURE 22. GATE DRIVE FALL TIME T_F vs TEMPERATURE



FIGURE 24. V_{LDEL}, V_{HDEL} VOLTAGE vs TEMPERATURE







FIGURE 23. GATE DRIVE RISE TIME T_R vs TEMPERATURE



FIGURE 25. HIGH LEVEL OUTPUT VOLTAGE, V_{CC} - V_{OH} vs BIAS SUPPLY AND TEMPERATURE AT 100μ A



FIGURE 27. PEAK PULLDOWN CURRENT I_{O-} BIAS SUPPLY VOLTAGE

Typical Performance Curves $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V, V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = V_{BHS} = 0V, R_{HDEL} = R_{LDEL} = 100K, and T_A = +25°C, Unless Otherwise Specified (Continued)$



1000 500 LEVEL-SHIFT CURRENT (µA) 200 100 50 20 10 10 20 50 100 200 500 1000 SWITCHING FREQUENCY (kHz)

FIGURE 30. HIGH VOLTAGE LEVEL-SHIFT CURRENT vs FREQUENCY AND BUS VOLTAGE



FIGURE 29. LOW VOLTAGE BIAS CURRENT I_{DD} AND I_{CC} (LESS QUIESCENT COMPONENT) vs FREQUENCY AND GATE LOAD CAPACITANCE



FIGURE 31. UNDERVOLTAGE LOCKOUT vs TEMPERATURE



FIGURE 32. MINIMUM DEAD-TIME vs DEL RESISTANCE





NOTES:

1. DEVICE CD4069UB PIN 7 = COM. PIN 14 = +12V.

2. COMPONENTS L1, L2, C1, C2, CX, CY, R30, R31, ARE NOT SUPPLIED. REFER TO APPLICATION NOTE FOR HELP IN DETERMINING JMPR1 - JMPR4 JUMPER LOCATIONS.

FIGURE 33. HIP4080A EVALUATION PC BOARD SCHEMATIC

HIP4080A



FIGURE 33. HIP4080A EVALUATION BOARD SILKSCREEN

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Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please visit our website to make sure you have the latest revision.

DATE	REVISION	CHANGE
Dec 11, 2019	FN3658.8	Removed retired parts. Added Revision History section. Updated POD M20.3 to the latest revision. Changes are as follows: Rev 2 Removed "u" symbol from drawing (overlaps the "a" on Side View). Rev 3 Top View: Corrected "7.50 BSC" to "7.60/7.40" (no change from rev 2; error was introduced in conversion) Changed "10.30 BSC" to "10.65/10.00" (no change from rev 2; error was introduced in conversion) Side View: Changed "12.80 BSC" to "13.00/12.60" (no change from rev 2; error was introduced in conversion) Changed "2.65 max" to "2.65/2.35" (no change from rev 2; error was introduced in conversion) Changed Note 1 from "ANSI Y14.5M-1982." to "ASME Y14.5M-1994" Updated to new POD format by moving dimensions from table onto drawing and adding land pattern Updated disclaimer.



Package Outline Drawings



NOTES:

- 3. Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- 4. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- 5. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- 6. Dimensions A, A1 and L are measured with the package seated in JEDEC seating plane gauge GS-3.
- 7. D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- 8. E and e_A are measured with the leads constrained to be perpendicular to datum -C-.
- 9. ${\bf e}_B$ and ${\bf e}_C$ are measured at the lead tips with the leads unconstrained. ${\bf e}_C$ must be zero or greater.
- 10. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- 11. N is the maximum number of terminal positions.
- 12. Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 0.045 inch (0.76 1.14mm).

E20.3 (JEDEC MS-001-AD ISSUE D) 20 LEAD DUAL-IN-LINE PLASTIC PACKAGE (PDIP)

	INC	HES	MILLIN	IETERS	
SYMBOL	MIN	MAX	MIN	MAX	NOTES
А	-	0.210	-	5.33	4
A1	0.015	-	0.39	-	4
A2	0.115	0.195	2.93	4.95	-
В	0.014	0.022	0.356	0.558	-
B1	0.045	0.070	1.55	1.77	8
С	0.008	0.014	0.204	0.355	-
D	0.980	1.060	24.89	26.9	5
D1	0.005	-	0.13	-	5
Е	0.300	0.325	7.62	8.25	6
E1	0.240	0.280	6.10	7.11	5
е	0.100	BSC	2.54	BSC	-
e _A	0.300) BSC	7.62	2 BSC	6
е _В	-	0.430	-	10.92	7
L	0.115	0.150	2.93	3.81	4
Ν	2	20	20		9

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M20.3 20 LEAD WIDE BODY SMALL OUTLINE PLASTIC PACKAGE (SOIC) Rev 3, 2/11





SIDE VIEW





(9.40mm)



NOTES:

8

MAX

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimension does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- 2. Dimension does not include interlead lash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 4. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 5. Dimension is the length of terminal for soldering to a substrate.
- 6. Terminal numbers are shown for reference only.
- 7. The lead width as measured 0.36mm (0.14 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch)
- 8. Controlling dimension: MILLIMETER.
- 9. Dimensions in () for reference only.
- 10. JEDEC reference drawing number: MS-013-AC.



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